

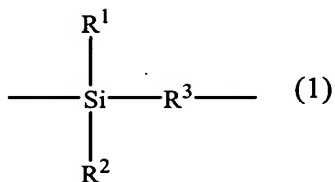
IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A ~~stopper for chemical mechanical planarization~~
stopper film present on the surface of a substrate, comprising:
an organosilicon polymer.

Claim 2 (Currently Amended): The stopper film ~~for chemical mechanical planarization~~
according to claim 1, wherein the organosilicon polymer is a polycarbosilane.

Claim 3 (Currently Amended): The stopper film ~~for chemical mechanical~~
~~planarization~~ according to claim 1, wherein the organosilicon polymer is at least one polymer
selected from the group consisting of polymers having the structural unit of the following
formula (1),



wherein R¹ and R² independently represent a hydrogen atom, an alkyl group having 1-30 carbon atoms that may have a substituent, an alkenyl group having 1-30 carbon atoms that may have a substituent, an alkynyl group having 1-30 carbon atoms that may have a substituent, or an aromatic group that may have a substituent and R³ represents -CC-, -CH₂- that may have a substituent linked with at least one -C≡C- group, an alkylene group having 2-30 carbon atoms that may have a substituent linked with at least one -C≡C- group, an alkenylene group having 2-30 carbon atoms that may have a substituent linked with at least one -C≡C- group, an alkynylene group having 2-30 carbon atoms that may have a substituent

linked with at least one $\text{-C}\equiv\text{C-}$ group, or a divalent aromatic group having 2-30 carbon atoms that may have a substituent linked with at least one $\text{-C}\equiv\text{C-}$ group.

Claim 4 (Withdrawn, Currently Amended): A ~~coating solution for forming a stopper~~ stopper coating solution, comprising:
a polycarbosilane and an organic solvent.

Claim 5 (Withdrawn, Currently Amended): A method for producing a stopper for chemical mechanical planarization, comprising:
applying a coating solution comprising (A) a polycarbosilane and (B) an organic solvent to a substrate, and
heating the coating.

Claim 6 (Withdrawn): A chemical mechanical planarization method for removing a metallic film formed on an insulating film using a polishing solution characterized by providing a stopper for chemical mechanical planarization comprising polycarbosilane between the insulating film and metal film.

Claim 7 (Withdrawn): The chemical mechanical planarization method according to claim 6, wherein the metallic film comprises a first metal film of a barrier metal and a second metal film of copper, an alloy containing copper as a main component, or a copper compound.

Claim 8 (Withdrawn): A chemical mechanical planarization method comprising

forming a layer having an opening on a semiconductor region, the layer comprising an insulating film formed on the semiconductor region and a stopper for chemical mechanical planarization formed on insulating film,

depositing a first metallic film of a barrier metal and a second metallic film of copper, an alloy containing copper as a main component, or a copper compound in the stopper for chemical mechanical planarization and the opening to fill the opening with the deposited metal films, and

removing the second metallic film on the stopper for chemical mechanical planarization using a chemical mechanical planarization solution.

Claim 9 (New): A two-layer film present on the surface of a substrate, comprising:
an insulating film directly in contact with the substrate, and
the chemical mechanical planarization stopper film according to claim 1.

Claim 10 (New): The chemical mechanical planarization stopper film according to claim 1, having a thickness in the dried state of from 0.02 to 1.5 micron.

Claim 11 (New): A substrate having a chemical mechanical planarization stopper film according to claim 1, present on a surface thereof, having a thickness of from 0.04 to 3 micron.

Claim 12 (New): The chemical mechanical planarization stopper film according to claim 1, wherein the substrate is a wafer.

Claim 13 (New): The chemical mechanical planarization stopper film according to claim 12, wherein the substrate is at least one selected from the group consisting of silicon, an SiO₂ wafer, an SiN wafer, an SiC wafer, an SiCO wafer, an SiCN wafer, and SiCON.

Claim 14 (New): The chemical mechanical planarization stopper film according to claim 1, wherein the organosilicon polymer comprises polymerized units of (phenylsilylene-ethynylene-1,3-phenylene-ethynylene).

Claim 15 (New): The chemical mechanical planarization stopper film according to claim 1, wherein the film consists of the organosilicon polymer.

Claim 16 (New): The two-layer film according to claim 9, wherein the insulating film comprises at least one selected from the group consisting of a polysiloxane film, a polysissequioxane film, a CVD-SiO₂ film, and a CVD-carbon doped SiO₂ film.

BASIS FOR THE AMENDMENT

Claims 1-16 are active in the present application. Claims 1-4 and 9-16 are currently under active prosecution. Claims 5-8 are non-elected claims presently withdrawn from prosecution. Claim 1 has been amended to state that the claimed invention is drawn to a chemical mechanical planarization stopper film. Support for the amendment is found throughout the specification, for example, in the Examples. Claims 9-16 are new claims. Support for new Claim 9 is found on page 4, lines 18-22. Support for new Claim 10 is found on page 15, lines 16-20. Support for new Claim 11 is found on page 15, lines 21-25. Support for new Claim 12 is found on page ?. Support for new Claim 13 is found on page 15, lines 5-10. Support for new Claim 14 is found on page 18, lines 12-14. Support for new Claim 15 is found on page 19, lines 11-16. Support for new Claim 13?, is found on page 15, lines 11-15. Support for new Claim 16 is found on page 15, lines 13-15. No new matter is added.